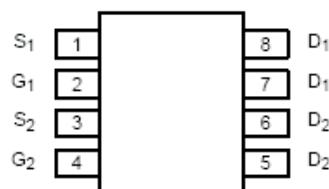
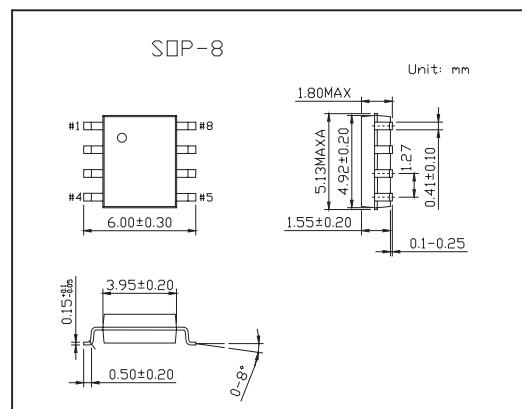
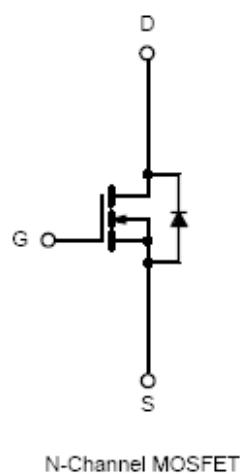


Dual N-Channel 80-V (D-S) MOSFET

KI4980DY

■ Features

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■ Absolute Maximum Ratings Ta = 25°C

Parameter		Symbol	Rating	Unit
Drain-Source Voltage		V _{DS}	80	V
Gate-Source Voltage		V _{Gs}	±20	
Continuous Drain Current (T _J = 150 °C)*	TA = 25 °C	I _D	3.7	A
	TA = 70 °C		2.9	
Pulsed Drain Current		I _{DM}	30	
Continuous Source Current (Diode Conduction) *		I _S	1.7	
Maximum Power Dissipation *	TA = 25 °C	P _D	2.0	W
	TA = 70 °C		1.3	
Operating Junction and Storage Temperature Range		T _J , T _{Stg}	-55 to 150	°C
Maximum Junction-to-Ambient*		R _{thJA}	62.5	°C/W

* Surface Mounted on FR4 Board, t ≤ 10 sec.

KI4980DY

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Gate Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250 μA	2			V
Gate-Body Leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ±20 V			±100	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 80 V, V _{GS} = 0 V		1		μ A
		V _{DS} = 80 V, V _{GS} = 0 V, T _J = 55°C		20		
On-State Drain Current *	I _{D(on)}	V _{DS} = 5 V, V _{GS} = 10 V	20			A
Drain-Source On-State Resistance*	r _{D(on)}	V _{GS} = 10 V, I _D = 3.7 A		0.062	0.075	Ω
		V _{GS} = 6.0 V, I _D = 3.2 A		0.071	0.095	Ω
Forward Transconductance*	g _{fs}	V _{DS} = 15 V, I _D = 3.7 A		12		S
Schottky Diode Forward Voltage*	V _{SD}	I _S = 1.7 A, V _{GS} = 0 V			1.2	V
Total Gate Charge	Q _g	V _{DS} = 40 V, V _{GS} = 10V, I _D = 3.7 A		15	30	nC
Gate-Source Charge	Q _{gs}			4		nC
Gate-Drain Charge	Q _{gd}			3.2		nC
Gate Resistance	R _g				5.1	Ω
Turn-On Delay Time	t _{d(on)}	V _{DD} = 40 V, R _L = 40 Ω I _D = 1 A, V _{GEN} = 10 V, R _G = 6 Ω		10	20	ns
Rise Time	t _r			10	20	ns
Turn-Off Delay Time	t _{d(off)}			30	60	ns
Fall Time	t _f			10	20	ns
Source-Drain Reverse Recovery Time	t _{rr}	I _F = 1.7 A, di/dt = 100 A/μ s		75	110	ns

* Pulse test; pulse width ≤ 300 μ s, duty cycle ≤ 2 %.